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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Kensaku MOTOKI, et al.
Patent No. : 6,773,504
Issued : August 10, 2004
Serial No. : 10/098,501 Art Unit : 1765
Filed : March 18, 2002 Examiner : Matthew A. Anderson
For : Oxygen Doping Method to Gallium Nitride Single Crystal Substrate and
Oxygen-Doped N-type Gallium Nitride Freestanding Single Crystal Substrate

CITATION BY PATENTEE UNDER 37 C.F.R. §1.501

Commissioner for Patents
P.O. Box 1450
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Sir:

It is respectfully requested that the attached cited document be placed in the official file for the above-identified patent application.

Still mindful of the duty of disclosure under 37 C.F.R. §1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) and a copy of the document cited thereon.

Applicants understand that this document and this paper simply will be placed in the official file for the subject application.

Respectfully submitted,
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